

Silicon NPN Power Transistors

2SC4026

DESCRIPTION

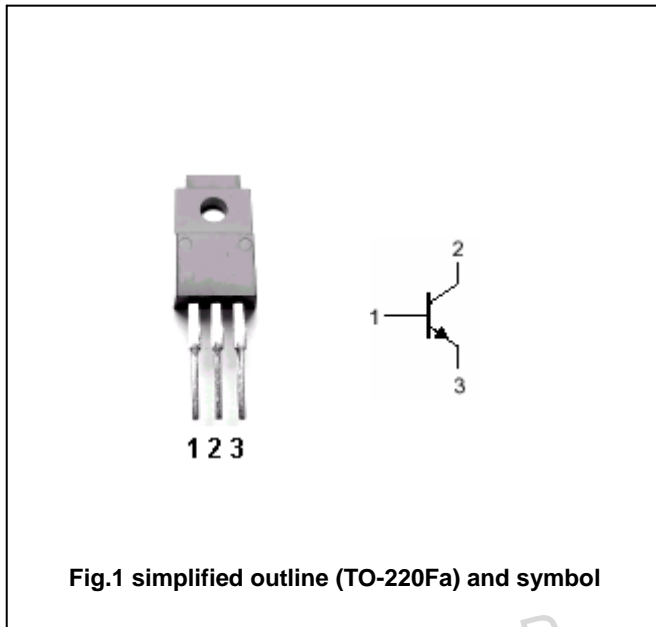
- With TO-220Fa package
- High breakdown voltage
- High speed switching
- Wide area of safe operation (SOA)

APPLICATIONS

- For high breakdown voltage high-speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		1.5	A
P _C	Collector power dissipation	T _C =25	35	W
		T _a =25	2	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

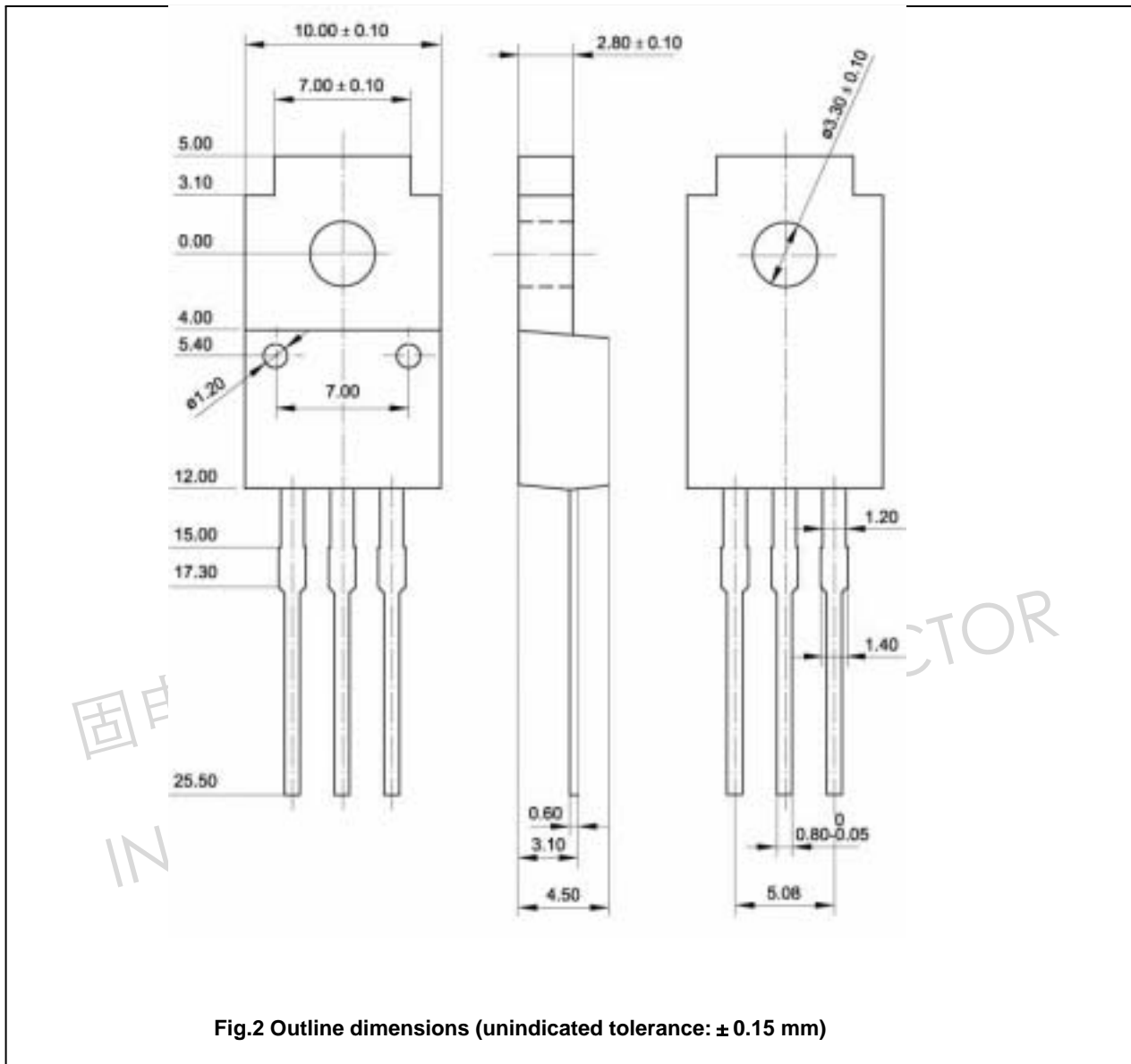
T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =0.1A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =2A; V _{CE} =5V	8			
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V; f=1MHz		5		MHz

Switching times

t _{on}	Turn-on time	I _C =2A; I _{B1} =0.4A; I _{B2} =-0.8A V _{CC} =150V			0.7	μs
t _s	Storage time				2.0	μs
t _f	Fall time				0.3	μs

PACKAGE OUTLINE



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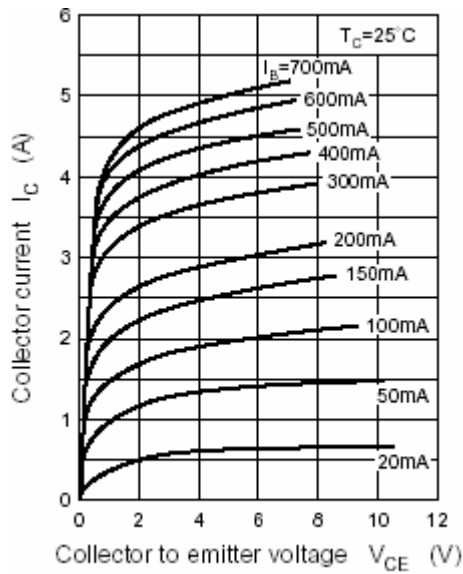


Fig.3 Static Characteristic

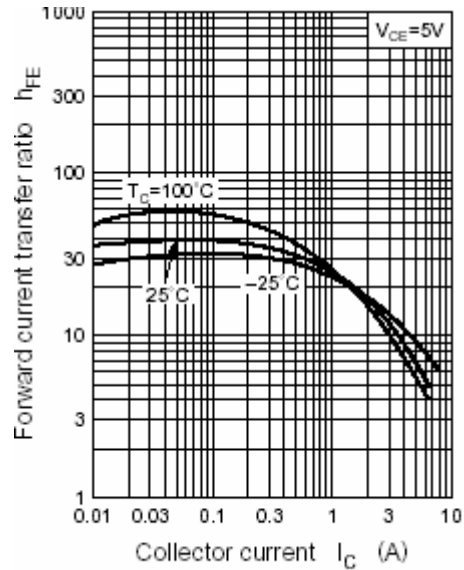


Fig.4 DC current Gain

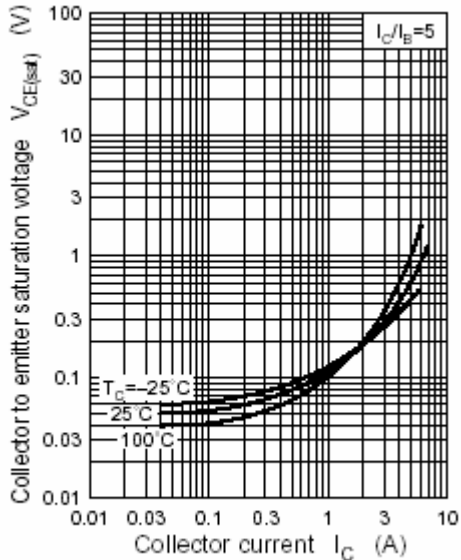


Fig.5 Collector-Emitter Saturation Voltage

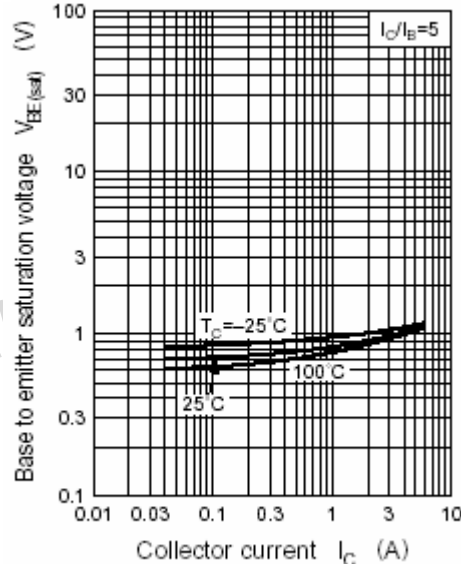


Fig.6 Base-Emitter Saturation Voltage

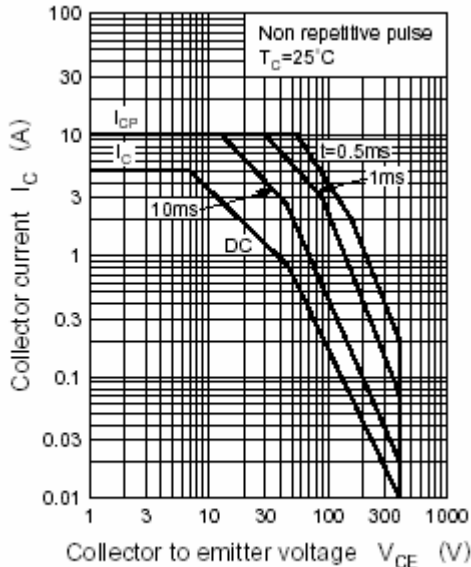


Fig.7 Safe Operating Area